



SD4V5FDTC

Single Line Bi-directional Transient Voltage Suppressor

DESCRIPTION

The SD4V5FDTC TVS diode is designed to replace multilayer varistors (MLVs) in portable applications such as cell phones, notebooks, and PDA's. It offers superior electrical characteristics such as low clamping voltage, low leakage current and high surge capability. It is designed to protect sensitive electronic components which are connected to power lines, from over-stress caused by ESD (Electrostatic Discharge), EFT (Electrical Fast Transients) and Lighting.

The SD4V5FDTC is in a DFN1610-2L package and will protect one bidirectional line. It may be used to provide ESD protection up to $\pm 30\text{kV}$ (Contact and air discharge) according to IEC61000-4-2, and withstand peak pulse current up to 160A (8/20 μs) according to IEC61000-4-5.

ORDERING INFORMATION

- ✧Device: SD4V5FDTC
- ✧Package: DFN1610-2L
- ✧Marking: D4N
- ✧Material: Halogen free and RoHS compliant
- ✧Packing: Tape & Reel
- ✧Quantity per reel: 3,000pcs

PIN CONFIGURATION



FEATURES

- ✧Transient protection for high-speed data lines
IEC 61000-4-2 (ESD) $\pm 30\text{kV}$ (Contact)
 $\pm 30\text{kV}$ (Air)
- ✧Peak power dissipation: 3200W (8/20 μs)
- ✧Working voltages : 4.5V
- ✧Low leakage current
- ✧Low clamping voltage
- ✧Ultra-small package (1.6mm·1.0mm·0.5mm)
- ✧Solid-state silicon-avalanche technology

MACHANICAL DATA

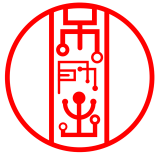
- ✧DFN1610-2L package
- ✧Flammability Rating: UL 94V-0
- ✧High temperature soldering guaranteed:
260C/10s
- ✧Packaging: Tape and Reel
- ✧Reel size: 7 inch

APPLICATIONS

- ✧Power lines
- ✧Personal digital assistants (PDA's)
- ✧Microprocessors based equipment
- ✧Notebooks, Desktops, and Servers
- ✧Cell phone Handsets and Accessories
- ✧Portable Electronics
- ✧Peripherals

PACKAGE OUTLINE





SD4V5FDTC

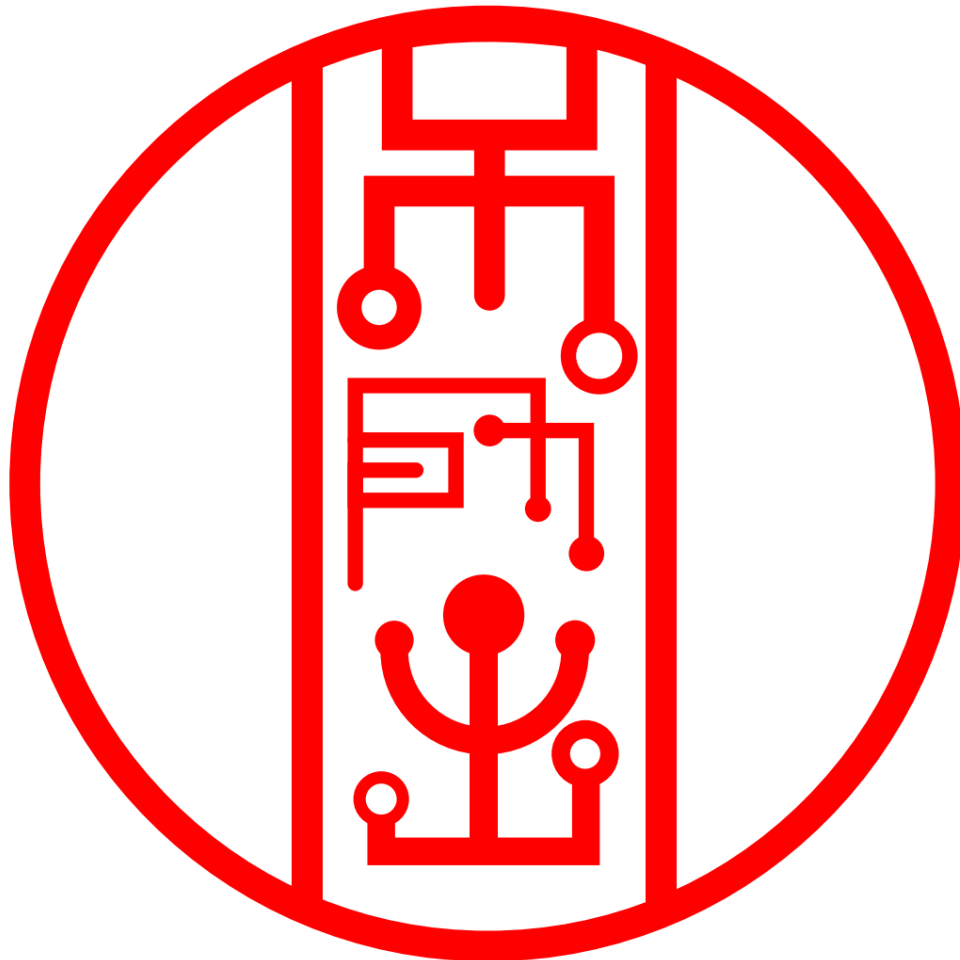
ABSOLUTE MAXIMUM RATING

Symbol	Parameter	Value	Units
V_{ESD}	ESD per IEC 61000-4-2 (Contact)	± 30	kV
	ESD per IEC 61000-4-2 (Air)	± 30	
P_{PP}	Peak Pulse Power (8/20 μ s)	3200	W
T_{OPT}	Operating Temperature	-55~125	$^{\circ}$ C
T_{STG}	Storage Temperature	-55~150	$^{\circ}$ C
T_L	Lead Soldering Temperature	260(10sec)	$^{\circ}$ C

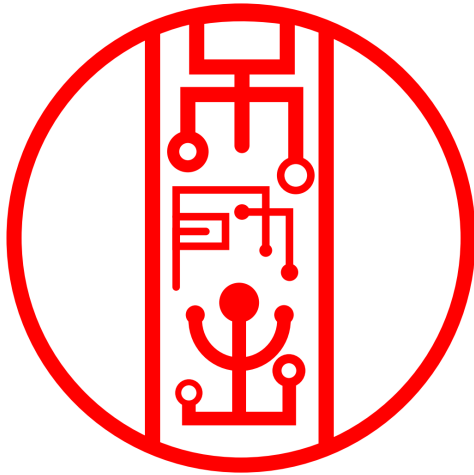
ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}$ C)

Symbol	Parameter	Test Condition	Min	Typ	Max	Units
V_{RWM}	Reverse Working Voltage				4.5	V
V_{BR}	Reverse Breakdown Voltage	$I_T = 1\text{mA}$	4.6	5.2	6.4	V
I_R	Reverse Leakage Current	$V_{RWM} = 4.5\text{V}$			1	μ A
I_{PP}	Peak Pulse Current	$t_p = 8/20\mu\text{s}$			160	A
V_C	Clamping Voltage	$I_{PP} = 50\text{A}, t_p = 8/20\mu\text{s}$		8.5	11	V
		$I_{PP} = 100\text{A}, t_p = 8/20\mu\text{s}$		12	14	V
		$I_{PP} = 160\text{A}, t_p = 8/20\mu\text{s}$		17	20	V
C_J	Junction Capacitance	$V_R = 0\text{V}, f = 1\text{MHz}$		300	500	pF

ELECTRICAL CHARACTERISTICS CURVE



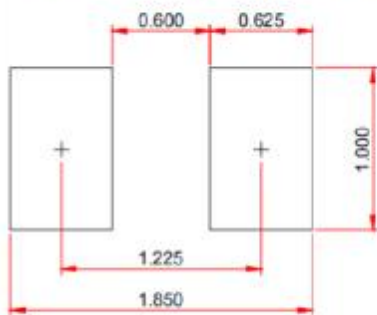
DFN1610-2L PACKAGE OUTLINE DIMENSIONS



NOTE: ALL DIMENSIONS IN MM

	MIN	NOM	MAX
D	0.95	1.00	1.05
E	1.55	1.60	1.65
L1	0.35	0.40	0.45
L2	0.35	0.40	0.45
A	0.45	0.50	0.55
b	0.85	0.90	0.95
e	1.1BSC		

Recommend Land Pattern (Unit: mm)



Note:

This recommended land pattern is for reference purpose only.